



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

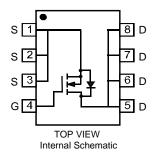
- Low On-Resistance
 - 14mΩ @ V_{GS} = 10V
 - 20mΩ @ V_{GS} = 4.5V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.072g (approximate)



TOP VIEW



Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Chara	acteristic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Drain Current (Note 3)	Steady State	T _A = 25°C T _A = 70°C	ID	9 7	A
Pulsed Drain Current (Note 4)			I _{DM}	50	А

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 3)	PD	1.46	W
Thermal Resistance, Junction to Ambient	R _{θJA}	86	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

3. Device mounted on FR-4 PCB, with minimum recommended pad layout.

4. Repetitive rating, pulse width limited by junction temperature.

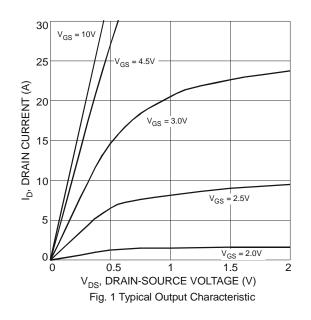


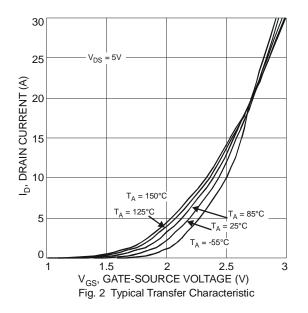
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	—		V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	—	_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	0.8	1.2	1.6	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			11	14	mΩ	$V_{GS} = 10V, I_D = 9A$	
Static Drain-Source On-Resistance	R _{DS} (ON)		14	20		$V_{GS} = 4.5V, I_D = 7A$	
Forward Transconductance	g fs	_	8		S	$V_{DS} = 10V, I_D = 9A$	
Diode Forward Voltage (Note 5)	V _{SD}	_	0.72	0.94	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{iss}	—	798		pF		
Output Capacitance	Coss	_	128		pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		122	_	pF	-1 = 1.0 WHz	
Gate Resistance	R _G	_	1.37	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz	
Total Gate Charge	Qg		8.7			V _{GS} = 5V, V _{DS} = 15V, I _D = 9A	
Gate-Source Charge	Q _{gs}	_	1.7		nC		
Gate-Drain Charge	Q _{gd}		2.4				
Turn-On Delay Time	t _{d(on)}		5.03	_		$\begin{split} V_{DD} &= 15V, V_{GEN} = 10V, \\ R_L &= 15\Omega, R_G = 6.0\Omega, I_D = 1A \end{split}$	
Rise Time	tr	_	4.50]		
Turn-Off Delay Time	t _{d(off)}		26.33	_	ns		
Fall Time	t _f		8.55		1		

Notes:

5. Short duration pulse test used to minimize self-heating effect.





DMN4800LSS



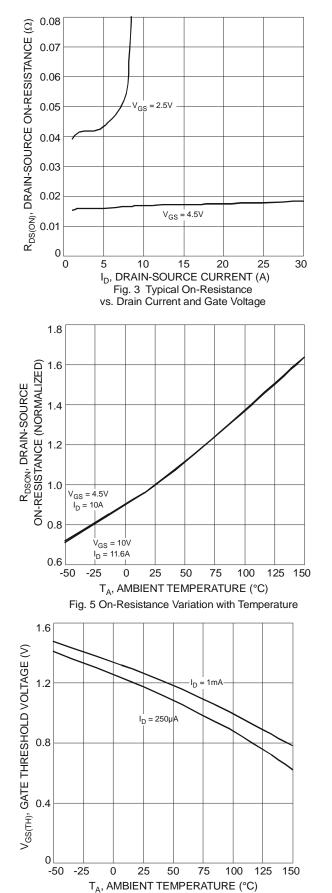


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

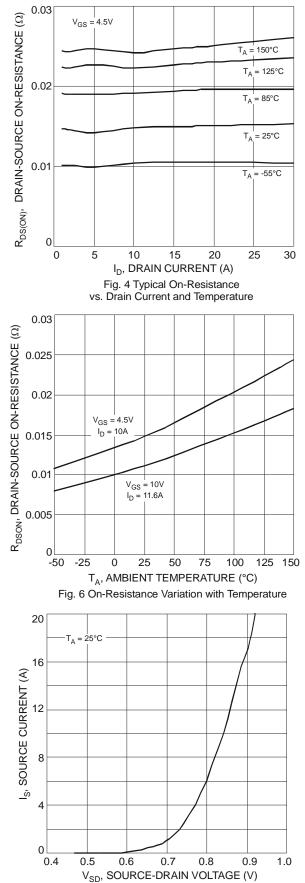
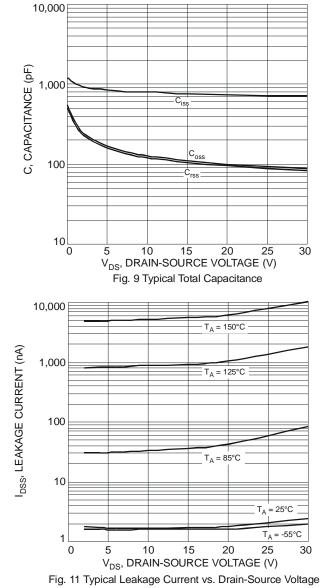
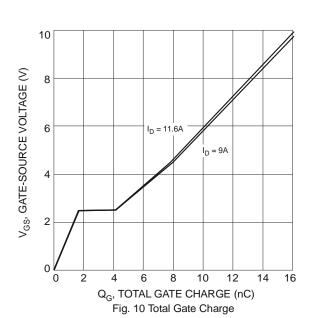


Fig. 8 Diode Forward Voltage vs. Current

NEW PRODUCT







r(t), TRANSIENT THERMAL RESISTANCE D = 0.7 D = 0.5 ++++ D = 0.3 0.1 D = 0.1 D = 0.9 D = 0.05 ----- $R_{\theta JA}(t) = r(t) * R_{\theta JA}$ D = 0.02 $R_{\theta JA} = 85^{\circ}C/W$ 0.01 D = 0.01 P(pk D = 0.005t₂ $T_J - T_A = P * R_{\theta JA}(t)$ Duty Cycle, $D = t_1/t_2$ -----D = Single Pulse 0.001 0.0001 0.001 0.01 0.1 10 100 1,000 1 t₁, PULSE DURATION TIME (s) Fig. 12 Transient Thermal Response

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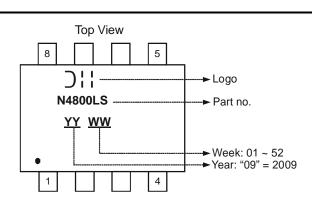


Ordering Information (Note 6)

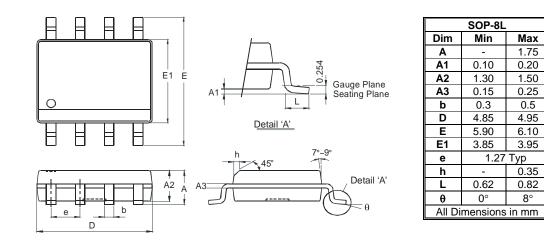
Case	Packaging
SOP-8L	2500/Tape & Reel
	SOP-8I

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

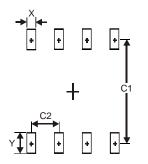
Marking Information



Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27

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